

SNXH80T120L2Q0SG

T-Type, Neutral Point Clamp Module

This high-density, integrated power module combines high-performance IGBTs with rugged anti-parallel diodes for sine wave inverter applications.

Features

- Extremely Efficient Trench IGBT with Fieldstop Technology
- Module Design Offers High Power Density
- Low Inductive Layout

Typical Applications

- Solar Inverters
- Uninterruptable Power Supplies

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
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BRIDGE IGBT

Collector-emitter voltage	V_{CES}	1200	V
Collector current $T_h = 80^\circ\text{C}$	I_C	65	A
Pulsed Collector Current, T_{pulse} Limited by T_{jmax}	I_{CM}	260	A
Gate-emitter voltage	V_{GE}	± 20	V
Power Dissipation per IGBT $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	146	W
Short Circuit Withstand Time $V_{GE} = 15\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J \leq 150^\circ\text{C}$	T_{SC}	10	μs

NEUTRAL POINT IGBT

Collector-emitter voltage (Bridge)	V_{CES}	600	V
Collector current @ $T_h = 80^\circ\text{C}$	I_C	59	A
Pulsed Collector Current, T_{pulse} Limited by T_{jmax}	I_{CM}	235	A
Gate-emitter voltage	V_{GE}	± 20	V
Power Dissipation per IGBT $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	66	W
Short Circuit Withstand Time $V_{GE} = 15\text{ V}$, $V_{CE} = 400\text{ V}$, $T_J \leq 150^\circ\text{C}$	T_{SC}	5	μs

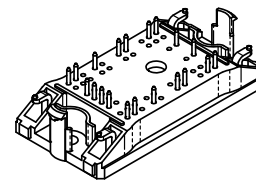
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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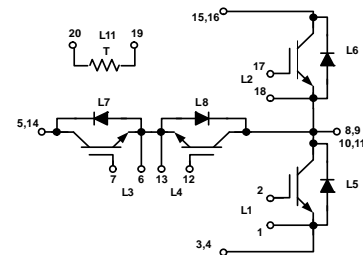
www.onsemi.com

80 A, 1200 V (Bridge)
50 A, 600 V (Neutral Point Clamp)
T – Type Neutral Point Clamp

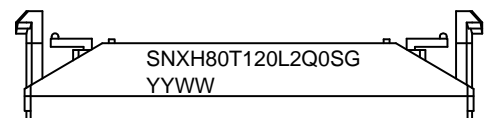


**Q0PACK
CASE 180AB**

SCHEMATIC



MARKING DIAGRAM



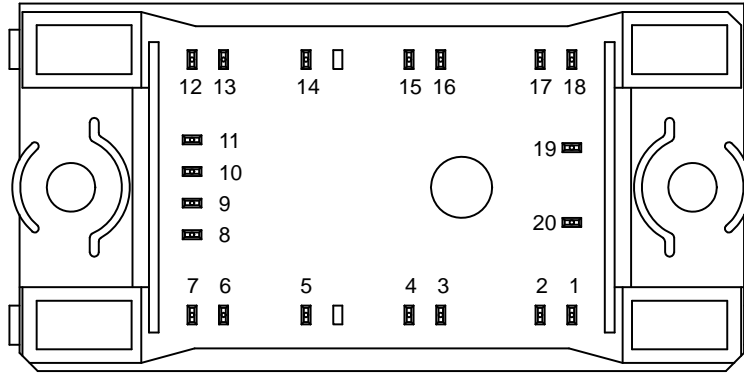
YYWW = Year and Work Week Code

ORDERING INFORMATION

See detailed ordering and shipping information in the dimensions section on page 13 of this data sheet.

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PIN ASSIGNMENTS



ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
BRIDGE DIODE			
Peak Repetitive Voltage	V_{RRM}	1200	V
Forward Current, DC @ $T_C = 80^\circ\text{C}$	I_F	41	A
Power Dissipation per Diode $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	69	W
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	300	A
I^2t – value (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I^2t	373.5	A^2s

NEUTRAL POINT DIODE

Diode peak repetitive voltage	V_{RRM}	600	V
Forward Current, DC @ $T_h = 80^\circ\text{C}$	I_F	36	A
Power Dissipation per Diode $T_j = T_{jmax}$ $T_h = 80^\circ\text{C}$	P_{total}	51	W
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	500	A
I^2t – value (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I^2t	1037.5	A^2s

THERMAL & SAFETY CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum junction temperature range IGBT Diode	T_J	175 175	$^\circ\text{C}$
Storage temperature range	T_{stg}	-40 to 150	$^\circ\text{C}$
Operating Temperature under Switching conditions	T_{VJOP}	-40 to 150	$^\circ\text{C}$
Isolation test voltage, $t = 1$ min, 60 Hz	V_{is}	2500	Vac
Creepage distance		12.7	mm
Clearance		12.7	mm

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit	
HALF BRIDGE IGBT CHARACTERISTICS							
Collector-emitter saturation voltage	V _{GE} = 15 V, I _C = 80 A, T _J = 25°C V _{GE} = 15 V, I _C = 80 A, T _J = 150°C	V _{CE(sat)}	1.7	2.17 2.20	2.7	V	
Gate-emitter threshold voltage	V _{GE} = V _{CE} , I _C = 1.5 mA	V _{GE(TH)}	5.0	6.0	6.5	V	
Collector-emitter cutoff current	V _{GE} = 0 V, V _{CE} = 1200 V	I _{CES}	–	–	200	μA	
Gate leakage current	V _{GE} = 20 V, V _{CE} = 0 V	I _{GES}	–	–	1.2	μA	
Turn-on delay time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	35	–	ns	
Rise time		t _r	–	28	–		
Turn-off delay time		t _{d(off)}	–	280	–		
Fall time		t _f	–	28	–		
Turn on switching loss		E _{on}	–	0.670	–		mJ
Turn off switching loss		E _{off}	–	1.3	–		
Turn-on delay time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	80	–	ns	
Rise time		t _r	–	30	–		
Turn-off delay time		t _{d(off)}	–	320	–		
Fall time		t _f	–	230	–		
Turn on switching loss		E _{on}	–	0.975	–		mJ
Turn off switching loss		E _{off}	–	3.00	–		
Input capacitance	V _{CE} = 20 V, V _{GE} = 0 V, f = 10 KHz	C _{ies}	–	19940	–	pF	
Output capacitance		C _{oes}	–	592	–		
Reverse transfer capacitance		C _{res}	–	383	–		
Gate charge total	V _{CE} = 960 V, I _C = 40 A, V _{GE} = ±15 V	Q _g	–	840	–	nC	
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		0.65		°C/W	

HALF BRIDGE DIODE CHARACTERISTICS

Forward voltage	V _{GE} = 0 V, I _F = 50 A, T _J = 25°C V _{GE} = 0 V, I _F = 50 A, T _J = 150°C	V _F	–	1.81 1.90	2.4	V
Reverse recovery time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.12	–	μs
Reverse recovery charge		Q _{rr}	–	4.7	–	μC
Peak reverse recovery current		I _{rrm}	–	135	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	7200	–	A/μs
Reverse recovery energy		E _{rr}	–	1.37	–	mJ
Reverse recovery time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.14	–	μs
Reverse recovery charge		Q _{rr}	–	7.65	–	μC
Peak reverse recovery current		I _{rrm}	–	138	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	4900	–	A/μs
Reverse recovery energy		E _{rr}	–	2.15	–	mJ
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		1.38		°C/W

NEUTRAL POINT CLAMP IGBT CHARACTERISTICS

Collector-emitter saturation voltage	V _{GE} = 15 V, I _C = 30 A, T _J = 25°C V _{GE} = 15 V, I _C = 30 A, T _J = 150°C	V _{CE(sat)}	1.1	1.3 1.3	1.6	V
Gate-emitter threshold voltage	V _{GE} = V _{CE} , I _C = 1.2 mA	V _{GE(TH)}	5.0	5.7	6.5	V
Collector-emitter cutoff current	V _{GE} = 0 V, V _{CE} = 600 V	I _{CES}	–	–	100	μA
Gate leakage current	V _{GE} = 20 V, V _{CE} = 0 V	I _{GES}	–	–	0.60	μA

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
NEUTRAL POINT CLAMP IGBT CHARACTERISTICS						
Turn-on delay time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	46	–	ns
Rise time		t _r	–	16	–	
Turn-off delay time		t _{d(off)}	–	125	–	
Fall time		t _f	–	60	–	
Turn on switching loss		E _{on}	–	0.668	–	mJ
Turn off switching loss		E _{off}	–	0.76	–	
Turn-on delay time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{d(on)}	–	48	–	ns
Rise time		t _r	–	22	–	
Turn-off delay time		t _{d(off)}	–	200	–	
Fall time		t _f	–	134	–	
Turn on switching loss		E _{on}	–	1.1	–	mJ
Turn off switching loss		E _{off}	–	2.5	–	
Input capacitance	V _{CE} = 20 V, V _{GE} = 0 V, f = 10 KHz	C _{ies}	–	9900	–	pF
Output capacitance		C _{oes}	–	270	–	
Reverse transfer capacitance		C _{res}	–	270	–	
Gate charge total	V _{CE} = 480 V, I _C = 75 A, V _{GE} = ±15 V	Q _G	–	390	–	nC
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		1.35		°C/W

NEUTRAL POINT CLAMP DIODE CHARACTERISTICS

Forward voltage	V _{GE} = 0 V, I _F = 60 A, T _J = 25°C V _{GE} = 0 V, I _F = 60 A, T _J = 150°C	V _F	–	1.7 1.8	2.0 –	V
Reverse recovery time	T _J = 25°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.04	–	μs
Reverse recovery charge		Q _{rr}	–	1.1	–	μC
Peak reverse recovery current		I _{rrm}	–	65	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	6600	–	A/μs
Reverse recovery energy		E _{rr}	–	0.384	–	mJ
Reverse recovery time	T _J = 150°C V _{CE} = 350 V, I _C = 56 A V _{GE} = ±15 V, R _G = 4 Ω	t _{rr}	–	0.1	–	μs
Reverse recovery charge		Q _{rr}	–	3.3	–	μC
Peak reverse recovery current		I _{rrm}	–	68	–	A
Peak rate of fall of recovery current		di/dt _{max}	–	1733	–	A/μs
Reverse recovery energy		E _{rr}	–	0.74	–	mJ
Thermal Resistance, chip-to-heatsink	Thermal grease thickness ≤ 50 μm λ = 1 W/mK	R _{θJH}		1.86		°C/W

THERMISTOR CHARACTERISTICS

Normal resistance		R		22		kΩ
Nominal resistance	T = 100°C	R		1468		Ω
Deviation of R25		ΔR/R	–5		5	%
Power dissipation		P _D		200		mW
Power dissipation constant				2		mW/K
B-value	B(25/50), tol ±3%				3950	K
B-value	B(25/100), tol ±3%				3998	K
NTC reference					B	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS – HALF BRIDGE

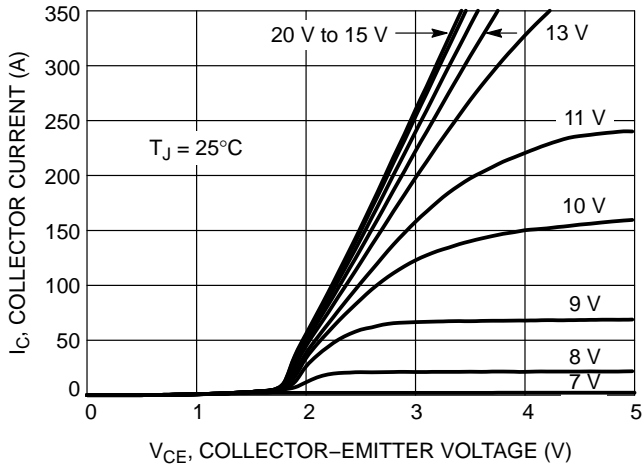


Figure 1. Output Characteristics

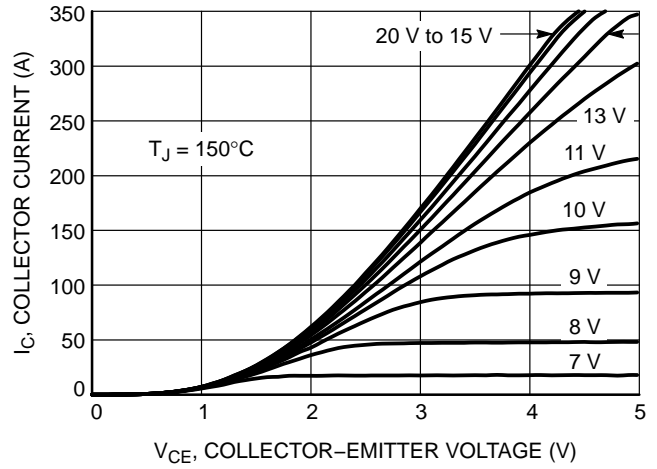


Figure 2. Output Characteristics

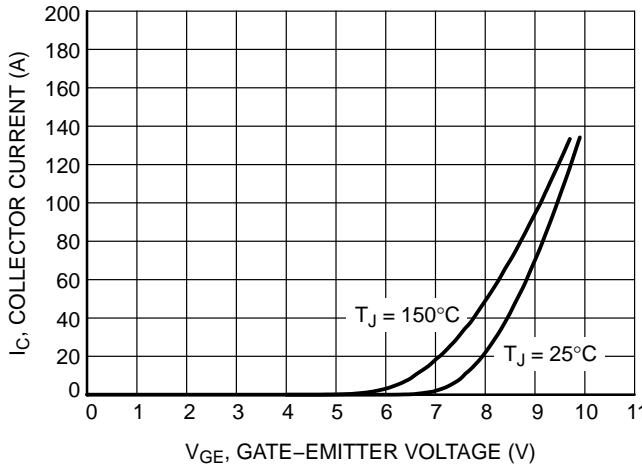


Figure 3. Typical Transfer Characteristics

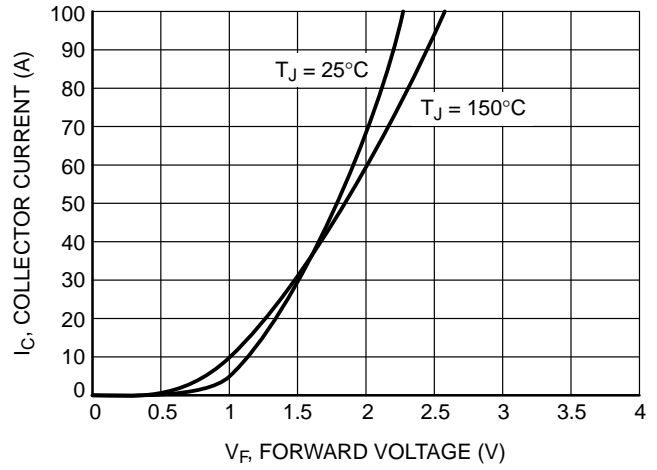


Figure 4. Diode Forward Characteristics

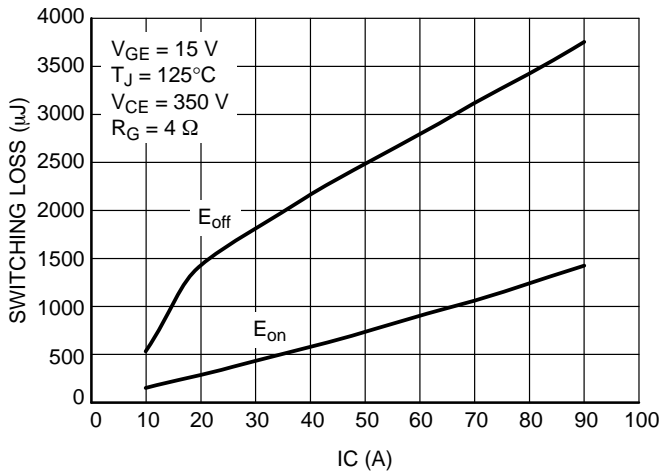


Figure 5. Typical Switching Loss vs. IC

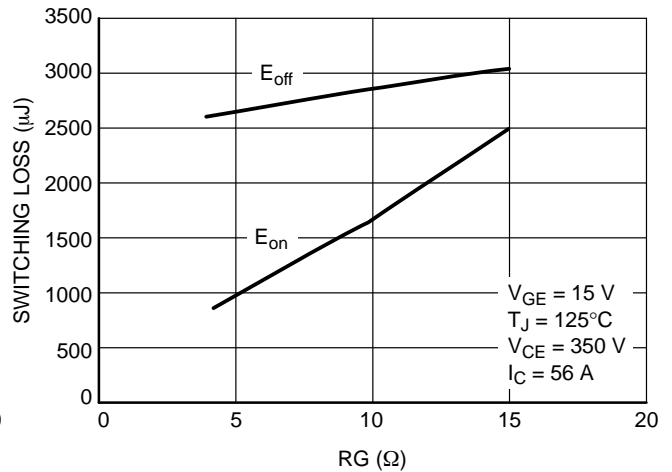


Figure 6. Typical Switching Loss vs. RG

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TYPICAL CHARACTERISTICS – HALF BRIDGE

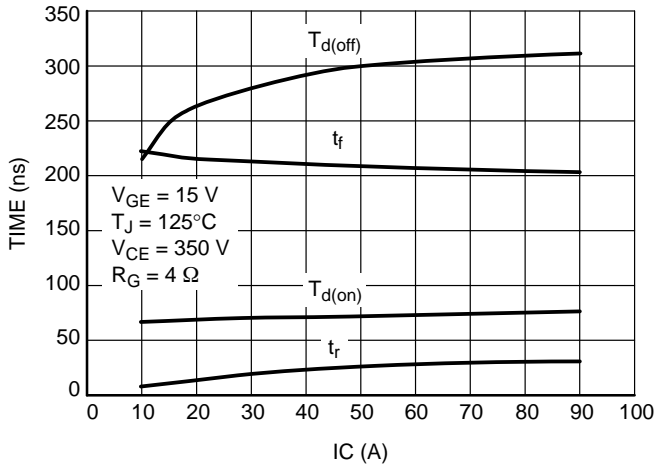


Figure 7. Typical Switching Time vs. IC

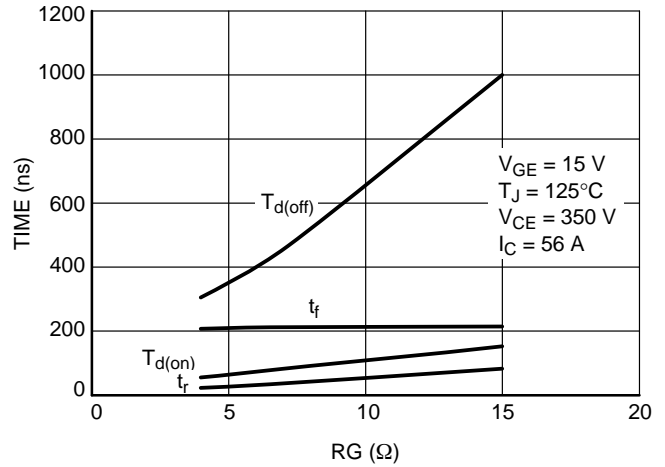


Figure 8. Typical Switching Time vs. RG

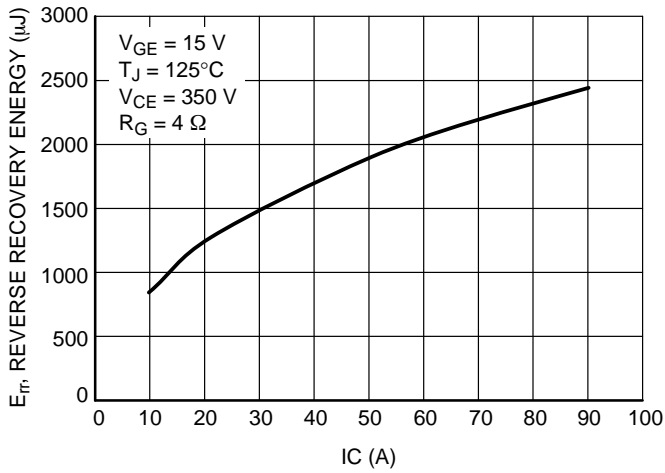


Figure 9. Typical Reverse Recovery Energy Loss vs. IC

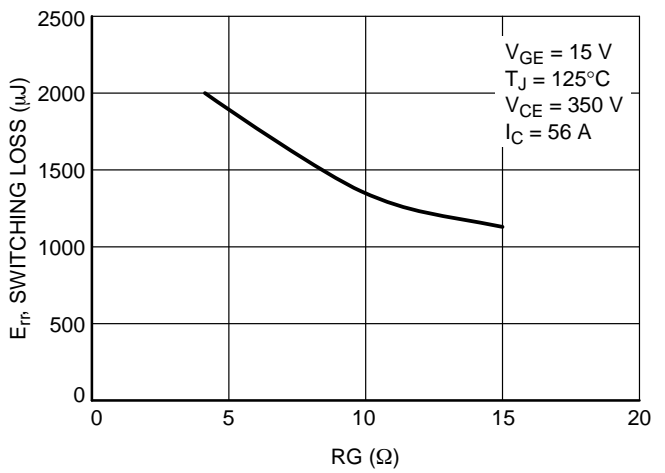


Figure 10. Typical Reverse Recovery Energy Loss vs. RG

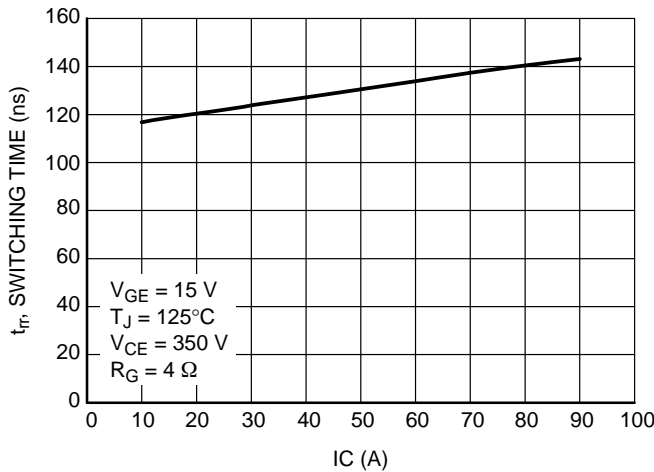


Figure 11. Typical Reverse Recovery Time vs. IC

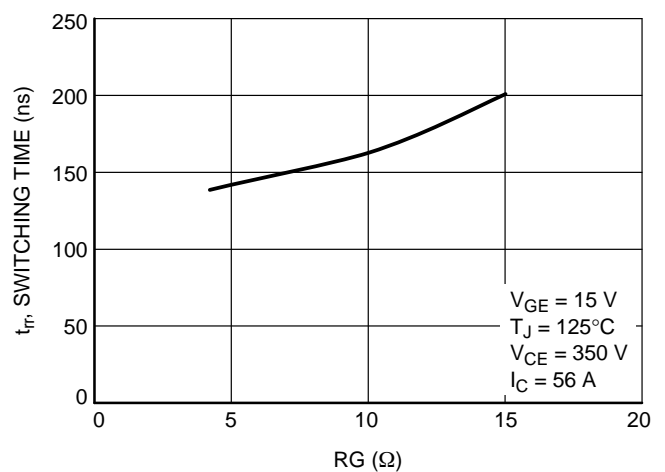


Figure 12. Typical Reverse Recovery Time vs. RG

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TYPICAL CHARACTERISTICS – HALF BRIDGE

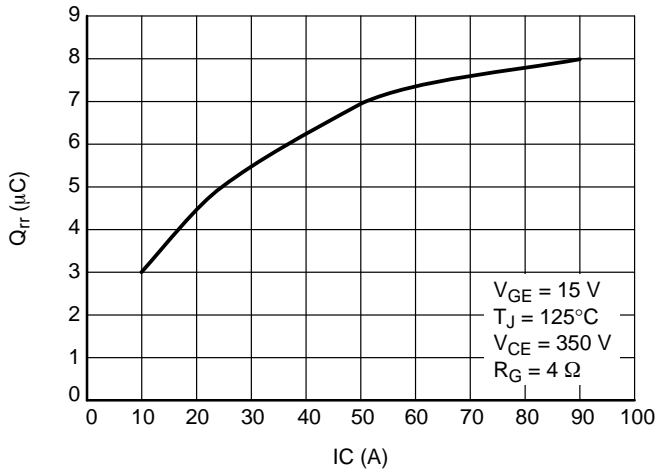


Figure 13. Typical Reverse Recovery Charge vs. IC

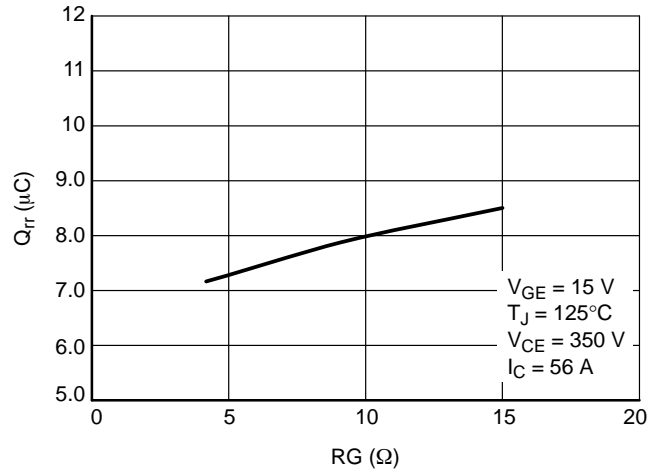


Figure 14. Typical Reverse Recovery Charge vs. RG

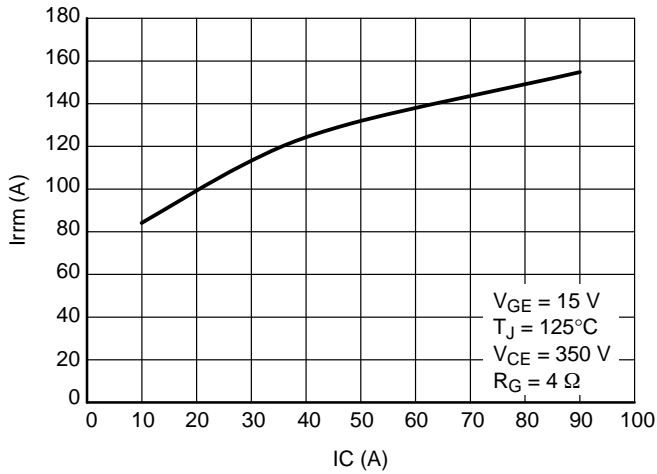


Figure 15. Typical Reverse Recovery Current vs. IC

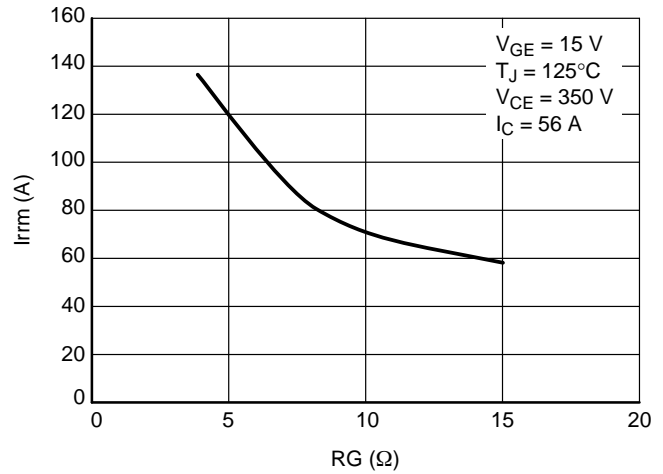


Figure 16. Typical Reverse Recovery Current vs. RG

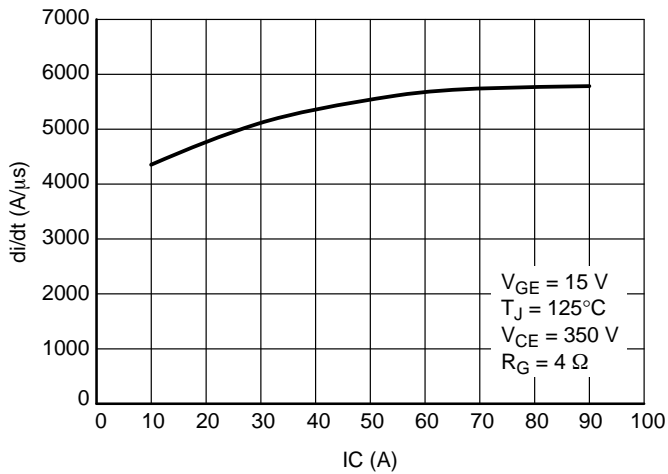


Figure 17. Typical di/dt vs. IC

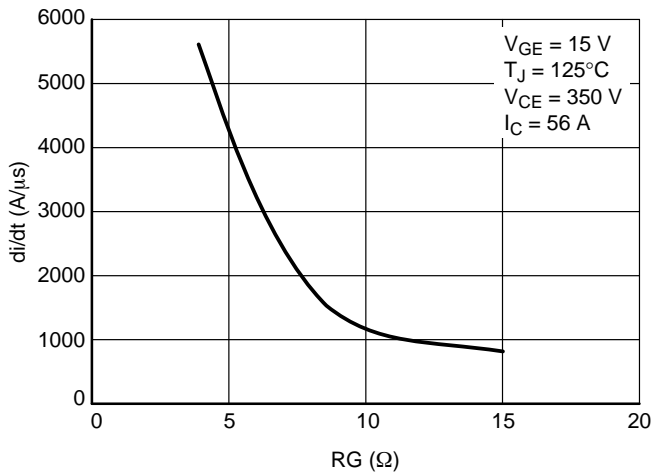


Figure 18. Typical di/dt vs. RG

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TYPICAL CHARACTERISTICS – HALF BRIDGE

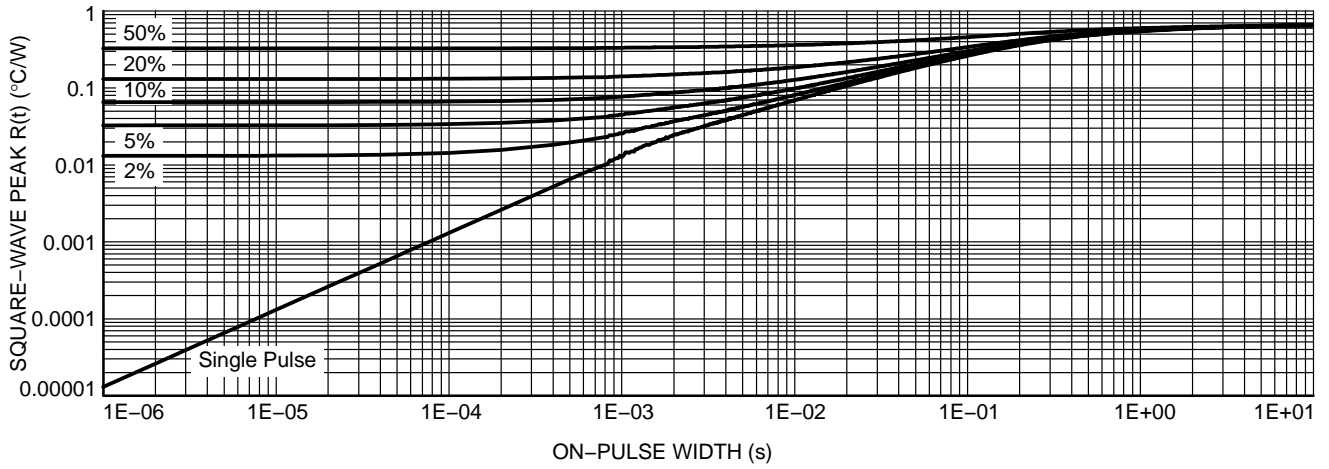


Figure 19. IGBT Transient Thermal Impedance

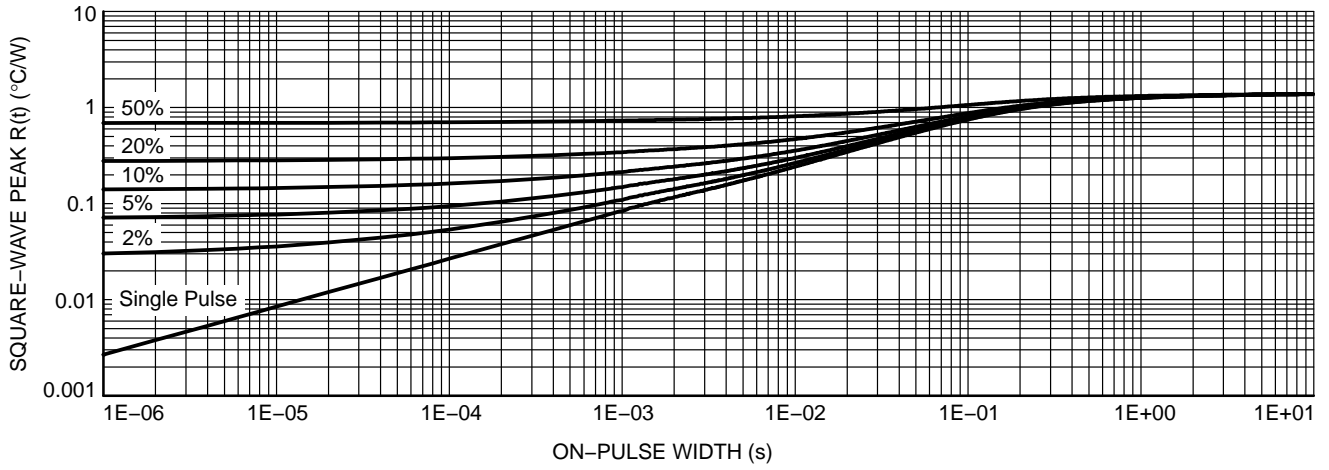


Figure 20. Diode Transient Thermal Impedance

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TYPICAL CHARACTERISTICS – NEUTRAL POINT

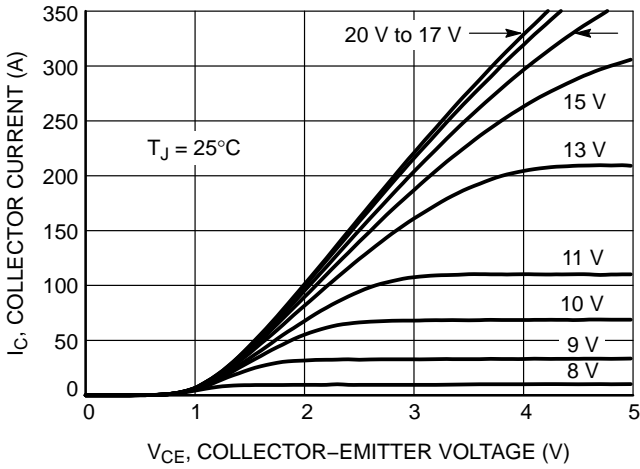


Figure 21. Output Characteristics

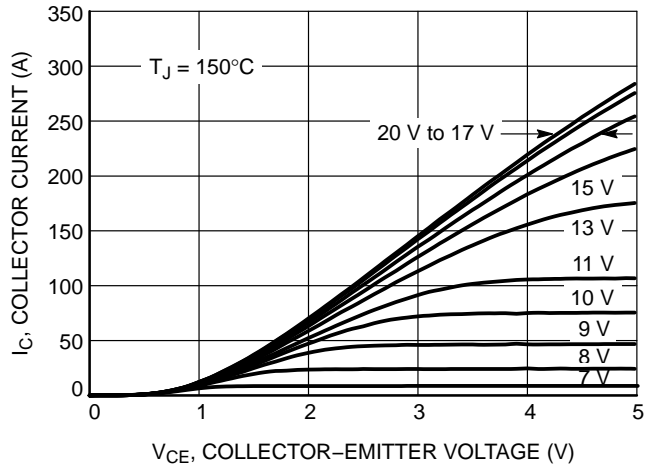


Figure 22. Output Characteristics

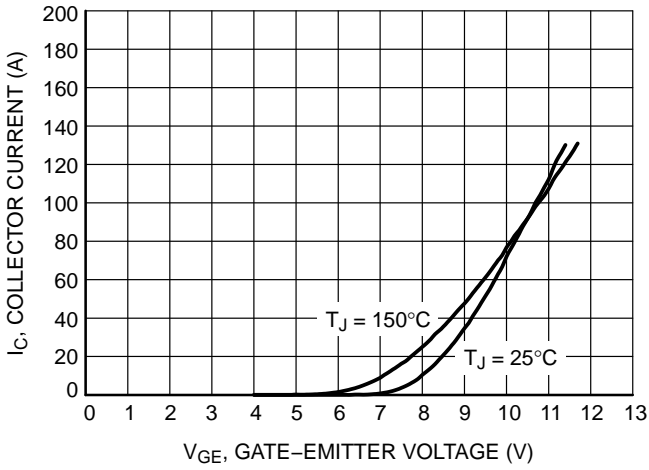


Figure 23. Typical Transfer Characteristics

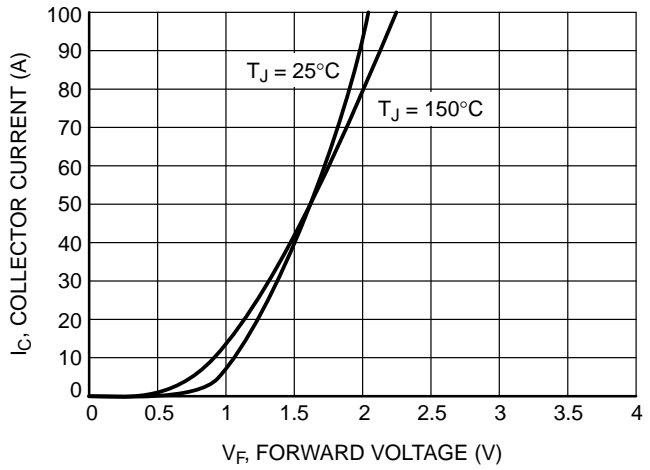


Figure 24. Diode Forward Characteristics

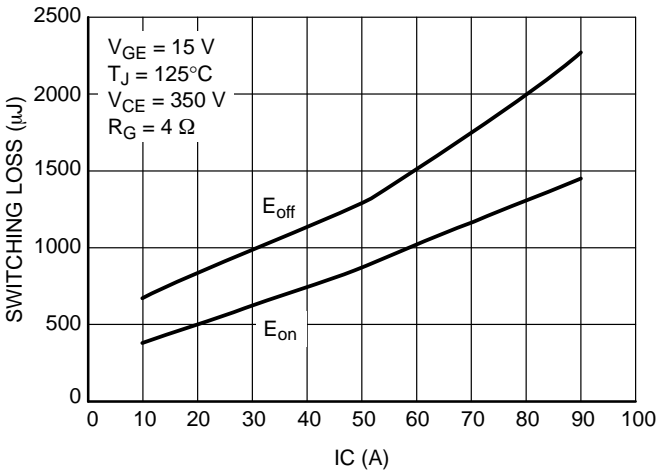


Figure 25. Typical Switching Loss vs. I_C

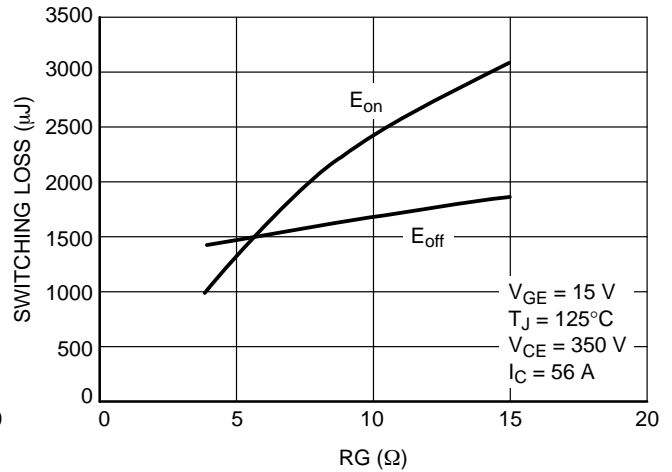


Figure 26. Typical Switching Loss vs. R_G

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TYPICAL CHARACTERISTICS – NEUTRAL POINT

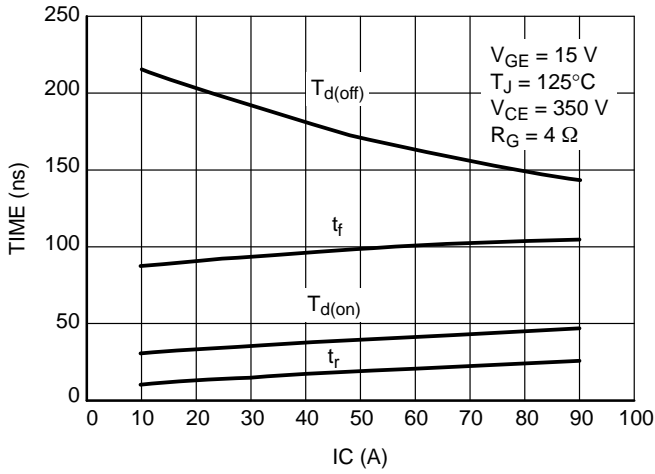


Figure 27. Typical Switching Time vs. IC

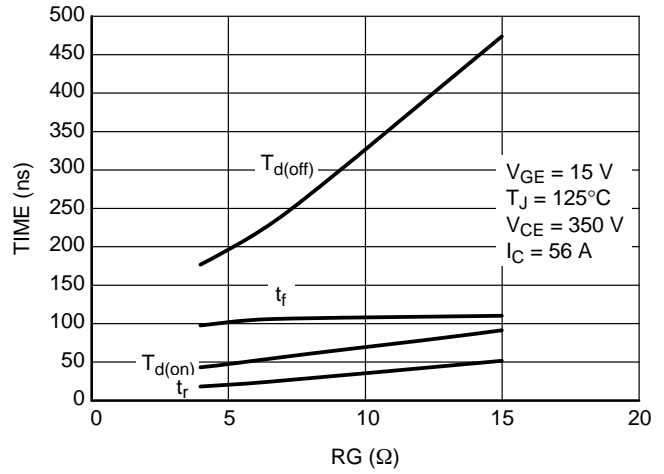


Figure 28. Typical Switching Time vs. R_G

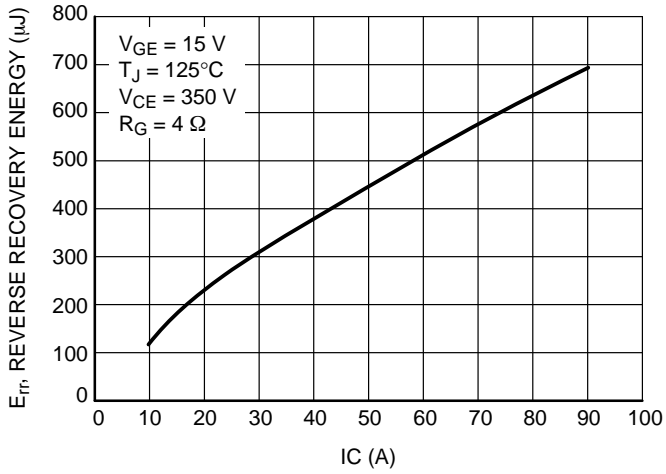


Figure 29. Typical Reverse Recovery Energy Loss vs. IC

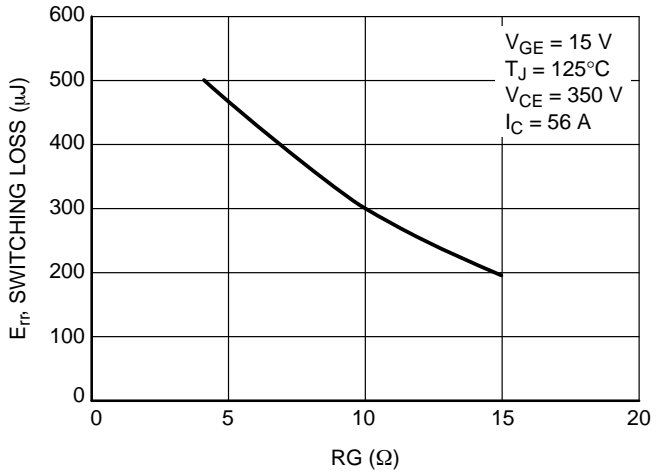


Figure 30. Typical Reverse Recovery Energy Loss vs. R_G

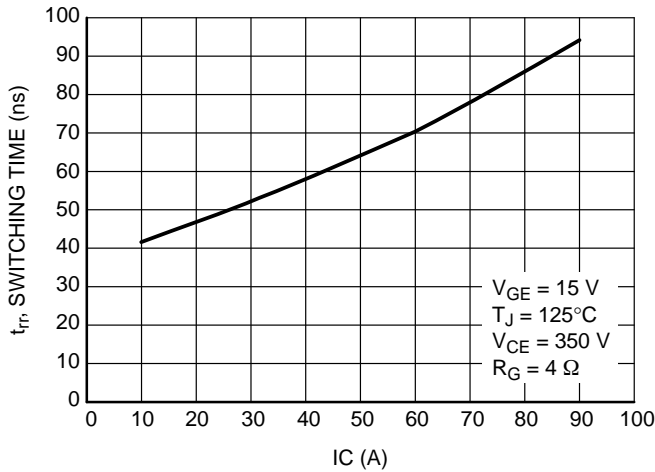


Figure 31. Typical Reverse Recovery Time vs. IC

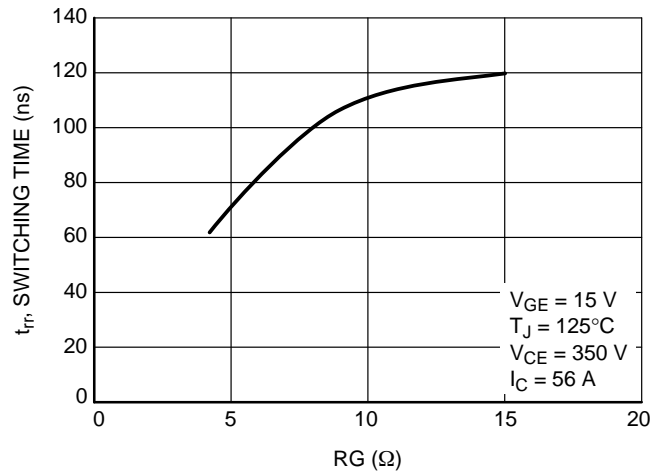


Figure 32. Typical Reverse Recovery Time vs. R_G

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TYPICAL CHARACTERISTICS – NEUTRAL POINT

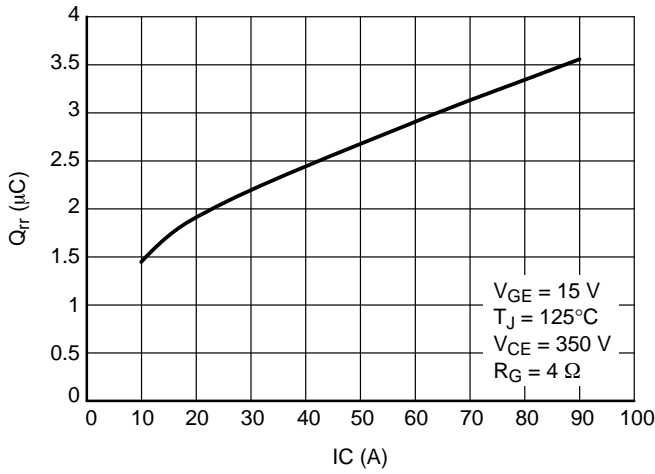


Figure 33. Typical Reverse Recovery Charge vs. IC

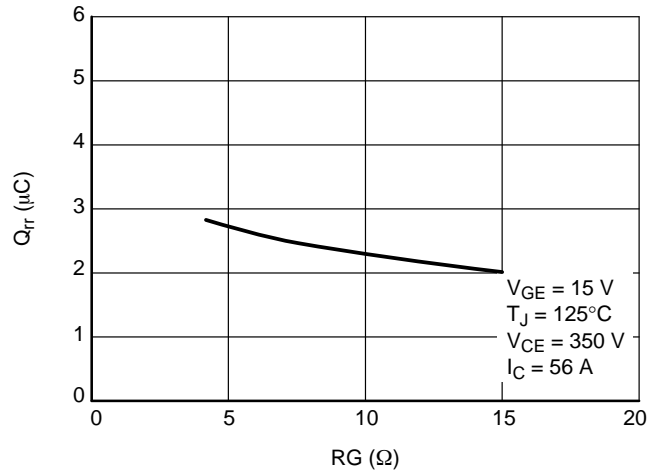


Figure 34. Typical Reverse Recovery Charge vs. RG

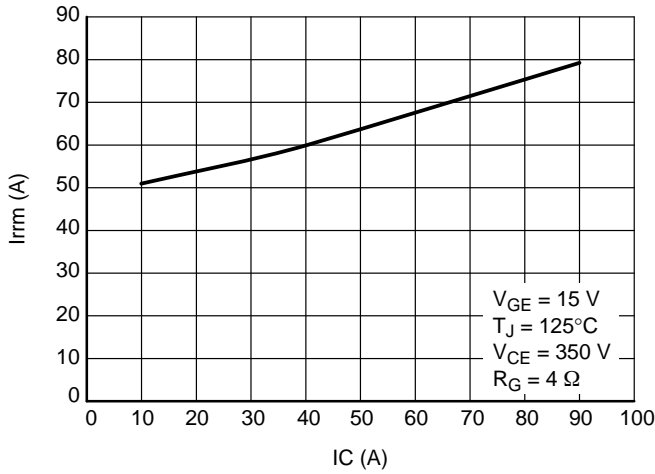


Figure 35. Typical Reverse Recovery Current vs. IC

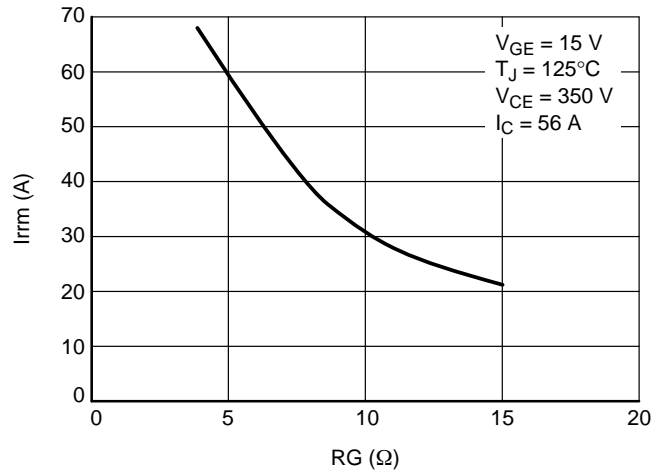


Figure 36. Typical Reverse Recovery Current vs. RG

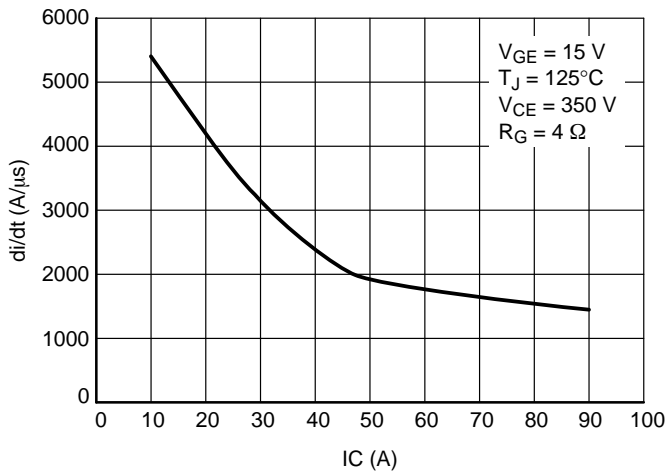


Figure 37. Typical di/dt vs. IC

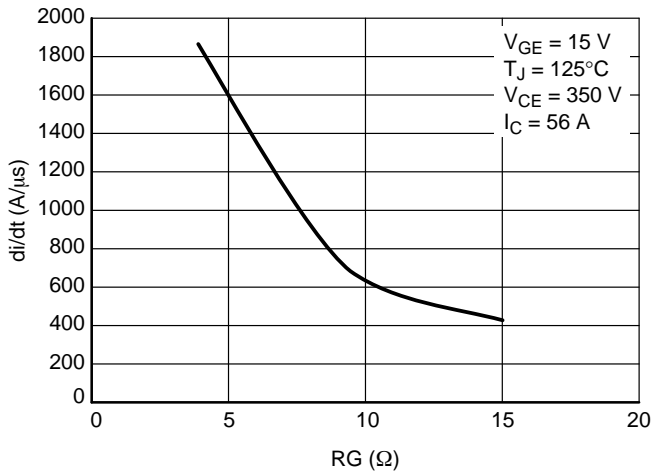


Figure 38. Typical di/dt vs. RG

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TYPICAL CHARACTERISTICS – NEUTRAL POINT

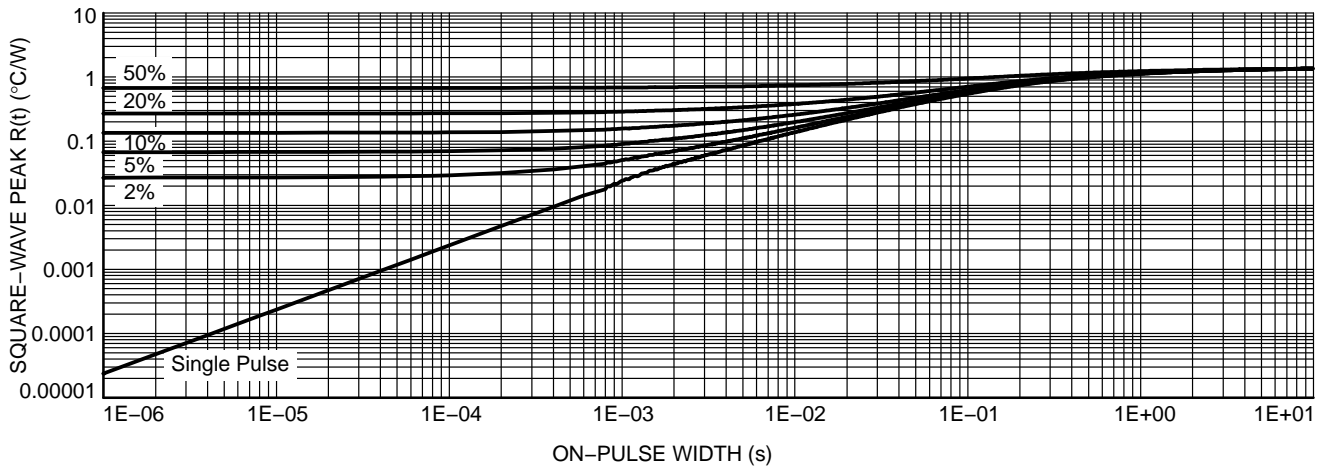


Figure 39. IGBT Transient Thermal Impedance

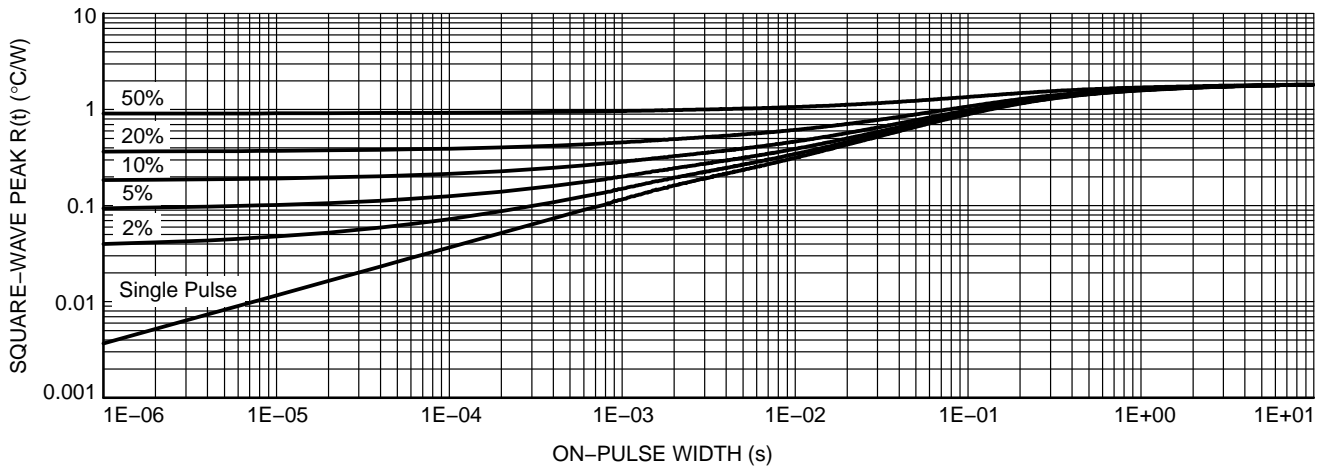


Figure 40. Diode Transient Thermal Impedance

SNXH80T120L2Q0SG

THERMISTOR CHARACTERISTICS

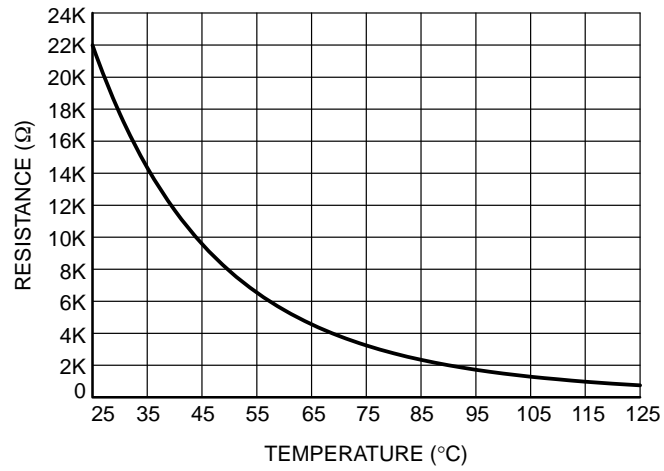


Figure 41. Thermistor Characteristics

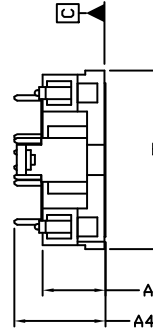
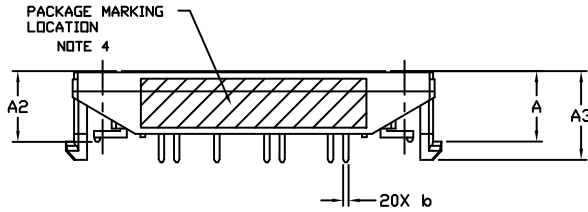
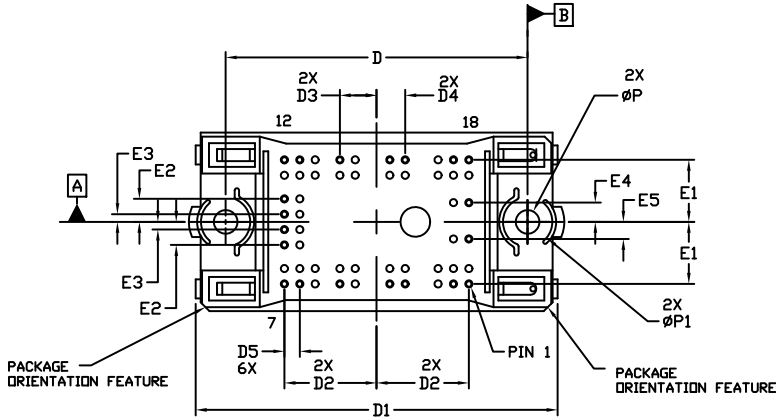
ORDERING INFORMATION

Orderable Part Number	Package	Shipping
SNXH80T120L2Q0SG (Solder Pin)	Q0PACK – Case 180AB (Pb-Free and Halide-Free)	24 Units / Blister Tray

SNXH80T120L2Q0SG

PACKAGE DIMENSIONS

PIM20, 55x32.5 / Q0PACK
CASE 180AB
ISSUE A



NOTES:

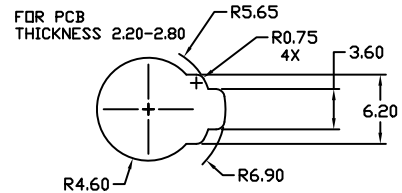
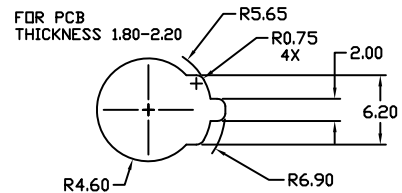
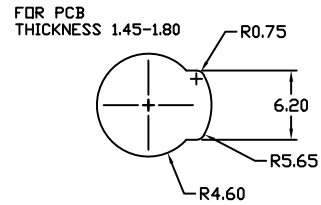
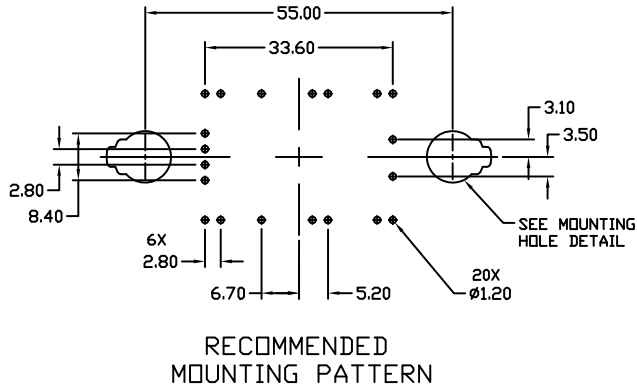
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO THE PLATED TERMINALS AND ARE MEASURED BETWEEN 1.00 AND 3.00 FROM TERMINAL TIP.
4. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.

DIM	MILLIMETERS	
	MIN.	NDM.
A	13.10	14.10
A1	10.75	11.75
A2	12.20	13.20
A3	15.45	16.45
A4	16.40	REF
b	0.95	1.05
D	54.80	55.20
D1	65.70	70.10
D2	16.80	BSC
D3	6.70	BSC
D4	5.20	BSC
D5	2.80	BSC
E	32.00	33.00
E1	11.30	BSC
E2	4.20	BSC
E3	1.40	BSC
E4	3.50	BSC
E5	3.10	BSC
P	4.10	4.50
P1	8.50	9.50


SNXH80T120L2Q0SG

PACKAGE DIMENSIONS

PIM20, 55x32.5 / Q0PACK
CASE 180AB
ISSUE A



MOUNTING HOLE DETAIL

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